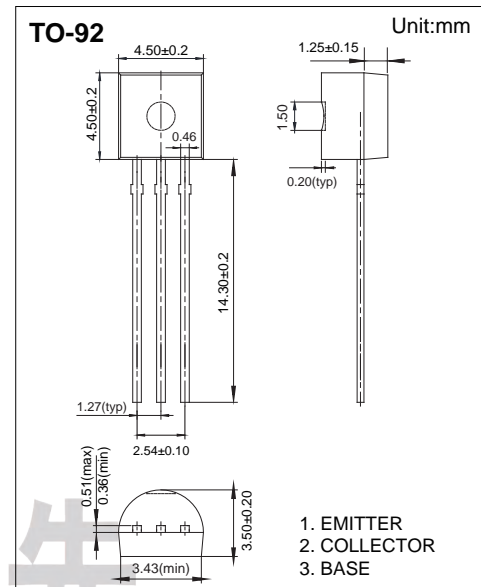


Transistor

PNP Transistors 2SB772S

■ Features

- High current output up to 3A
- Low saturation voltage
- Complement to 2SD882S



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-40	V
Collector - Emitter Voltage	V_{CE0}	-30	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-3	A
Peak Collector Current	I_{CP}	-7	
Base Current	I_B	-0.6	
Collector Power Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _c = -100 μA, I _E =0	-40			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B =0	-30			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _c =0	-5			
Collector cut-off current	I _{CBO}	V _{CB} = -30 V, I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-30V, I _B =0			-1	
Emitter cut-off current	I _{EBO}	V _{EB} = -3V, I _c =0			-1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-2 A, I _B = -200mA			-0.5	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =-2 A, I _B = -200mA			-2	
DC current gain (Note.1)	h _{FE(1)}	V _{CE} = -2V, I _c = -20mA	30			
	h _{FE(2)}	V _{CE} = -2V, I _c = -1 A	100		400	
Output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		45		pF
Transition frequency	f _t	V _{CE} = -5V, I _c = -100mA		80		MHz

Note.1:Pulse test: Pw<300μs, Duty Cycle<2%

■ Classification of h_{FE(2)}

Rank	Q	P	E
Range	100-200	160-320	200-400

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■ Typical Characteristics

